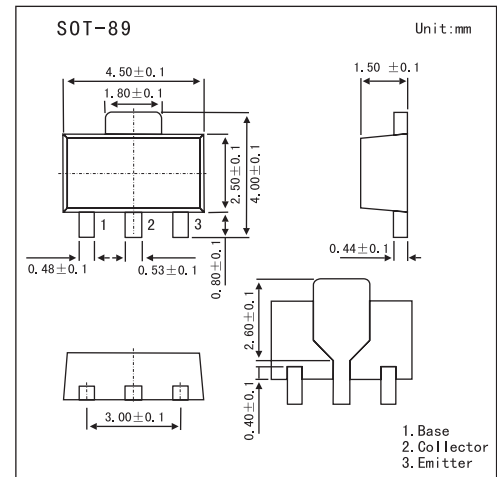


PNP Epitaxial Planar Silicon Transistors

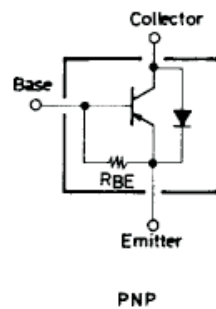
2SB1325

■ Features

- Low saturation voltage.
- Contains diode between collector and emitter.
- Contains bias resistance between base and emitter.
- Large current capacity.
- Small-sized package making it easy to provide highdensity, small-sized hybrid ICs.



■ Electrical Connection

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-25	V
Collector-emitter voltage	V_{CEO}	-20	V
Emitter-base voltage	V_{EBO}	-6	V
Collector current	I_C	-4	A
Collector current (pulse)	I_{CP}	-6	A
Collector dissipation	P_C *	1.5	W
Jumction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

* Mounted on ceramic board (250mm²X0.8mm)

2SB1325

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cutoff current	ICBO	V _{CB} = 20V , I _E = 0			-1	μA
DC current Gain	h _{FE}	V _{CE} = -2V , I _C = -0.5A	70			
		V _{CE} = -2V , I _C = -3A	50			
Gain bandwidth product	f _T	V _{CE} = -2V , I _C = -0.5A		300		MHz
Output capacitance	C _{ob}	V _{CB} = -10V , f = 1MHz		60		pF
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -3A , I _B = -150mA		-0.25	-0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	V _{CE} = -3V , I _C = -150mA			-1.5	V
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -10μA , I _E = 0	-25			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = -10μA , R _{BE} = ∞	-25			V
Base-emitter on state voltage	V _{(BR)CEO}	I _C = -10mA , R _{BE} = ∞	-20			V
Diode forward voltage	V _F	I _F =0.5A			1.5	V
Base-emitter resistance	R _{BE}			1.5		KΩ

■ Marking

Marking	BM
---------	----